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# FAIRCHILD

SEMICONDUCTOR

# MM74C221 **Dual Monostable Multivibrator**

#### **General Description**

The MM74C221 dual monostable multivibrator is a monolithic complementary MOS integrated circuit. Each multivibrator features a negative-transition-triggered input and a positive-transition-triggered input, either of which can be used as an inhibit input, and a clear input.

Once fired, the output pulses are independent of further transitions of the A and B inputs and are a function of the external timing components  $C_{\mathsf{EXT}}$  and  $R_{\mathsf{EXT}}$ . The pulse width is stable over a wide range of temperature and  $V_{CC}$ .

Pulse stability will be limited by the accuracy of external timing components. The pulse width is approximately defined by the relationship  $t_{W(OUT)}\approx C_{EXT}~R_{EXT}.$  For further information and applications, see AN-138.

#### **Features**

- Wide supply voltage range: 4.5V to 15V
- Guaranteed noise margin: 1.0V

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- High noise immunity: 0.45 V<sub>CC</sub> (typ.)
- Low power TTL compatibility: fan out of 2 driving 74L

## **Ordering Code:**

Order Number	Package Number	Package Description		
74MMC221N	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide		

#### **Connection Diagrams Truth Table** Inputs **Timing Component** Clear ę 1 Х REXT Х Н TO R/C<sub>EXT</sub> TERMINAL Н TO C<sub>ext</sub> Terminal H = HIGH Leve L = LOW Level 1 R/C<sub>EXT</sub> 1 C<sub>ext</sub> 10 2ū 2 CLR 2 R X= Irrelevant 12 = Transition from LOW-to-HIGH 13 11 $\downarrow$ = Transition from HIGH-to-LOW \_\_ = One HIGH Level Pulse -ur = One LOW Level Pulse ١Ď 1B 1 CLR 20 2 C<sub>EXT</sub> $2 \text{ R/C}_{\text{EXT}}$ GND **Top View**

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Outputs

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## Absolute Maximum Ratings(Note 1)

Voltage at Any Pin	–0.3V to V <sub>CC</sub> + 0.3V
Operating Temperature Range	$-55^{\circ}C$ to $+125^{\circ}C$
Storage Temperature Range	$-65^{\circ}C$ to $+150^{\circ}C$
Power Dissipation	
Dual-In-Line	700 mW
Small Outline	500 mW
Operating V <sub>CC</sub> Range	4.5V to 15V
Absolute Maximum V <sub>CC</sub>	18V
$R_{EXT} \ge 80 V_{CC} (\Omega)$	
Lead Temperature	
(Soldering, 10 seconds)	260°C

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The Electrical Characteristics table provides conditions for activit device accented to the safety of the device activity device accented to the safety of the device accented to the sa for actual device operation.

## **DC Electrical Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Units
CMOS to (	смоз					
V <sub>IN(1)</sub>	Logical "1" Input Voltage	$V_{CC} = 5V$	3.5			
		$V_{CC} = 10V$	8.0			V
VIN(0)	Logical "0" Input Voltage	$V_{CC} = 5V$			1.5	
		$V_{CC} = 10V$			2.0	V
V <sub>OUT(1)</sub>	Logical "1" Output Voltage	$V_{CC} = 5V, I_{O} = -10 \ \mu A$	4.5			
		$V_{CC} = 10V, I_{O} = -10 \ \mu A$	9.0			V
V <sub>OUT(0)</sub>	Logical "0" Output Voltage	$V_{CC} = 5V, I_{O} = +10 \ \mu A$			0.5	
		$V_{CC} = 10V, I_{O} = +10 \ \mu A$			1	V
I <sub>IN(1)</sub>	Logical "1" Input Current	V <sub>CC</sub> = 15V, V <sub>IN</sub> = 15V		0.005	1.0	μΑ
I <sub>IN(0)</sub>	Logical "0" Input Current	V <sub>CC</sub> = 15V, V <sub>IN</sub> = 0V	-1.0	-0.005		μΑ
Icc	Supply Current (Standby)	V <sub>CC</sub> = 15V, R <sub>EXT</sub> = ∞,		0.05	300	μA
		Q1, Q2 = Logic "0" (Note 2)				
Icc	Supply Current	V <sub>CC</sub> = 15V, Q1 = Logic "1",		15		mA
	(During Output Pulse)	Q2 = Logic "0" (Figure 4)				
		V <sub>CC</sub> = 5V, Q1 = Logic "1",		2		mA
		Q2 = Logic "0" (Figure 4)				
	Leakage Current at R/C <sub>EXT</sub> Pin	V <sub>CC</sub> = 15V, V <sub>CEXT</sub> = 5V		0.01	3.0	μΑ
CMOS/LP	TTL Interface	- I	1			
V <sub>IN(1)</sub>	Logical "1" Input Voltage	V <sub>CC</sub> = 4.75V	V <sub>CC</sub> – 1.5			V
VIN(0)	Logical "0" Input Voltage	$V_{CC} = 4.75V$			0.8	V
V <sub>OUT(1)</sub>	Logical "1" Output Voltage	$V_{CC} = 4.75 V, I_{O} = -360 \ \mu A$	2.4			V
V <sub>OUT(0)</sub>	Logical "0" Output Voltage	$V_{CC} = 4.75 V$ , $I_{O} = 360 \ \mu A$			0.4	V
Output Dr	ive (See Family Characteristics Data	Sheet) (Short Circuit Current)	1			
ISOURCE	Output Source Current	$V_{CC} = 5V$	-1.75			mA
	(P-Channel)	$T_A = 25^{\circ}C, \ V_{OUT} = 0V$				
ISOURCE	Output Source Current	$V_{CC} = 10V$	-8			mA
	(P-Channel)	$T_A = 25^{\circ}C, V_{OUT} = 0V$				
I <sub>SINK</sub>	Output Sink Current	$V_{CC} = 5V$	1.75			mA
	(N-Channel)	$T_A = 25^{\circ}C, V_{OUT} = V_{CC}$				
I <sub>SINK</sub>	Output Sink Current	V <sub>CC</sub> = 10V	8			mA
	(N-Channel)	$T_A = 25^{\circ}C, V_{OUT} = V_{CC}$				

by (Q = Logic "0") the power dissipated equals the leakage current plus  $V_{CC}/R_{EXT}$ .

	C, $C_L = 50$ pF, unless otherwise noted			-		
Symbol	Parameter	Conditions	Min	Тур	Max	Units
t <sub>pd A, B</sub>	Propagation Delay from Trigger	$V_{CC} = 5V$		250	500	ns
	Input (A, B) to Output Q, Q	V <sub>CC</sub> = 10V		120	250	<u> </u>
t <sub>pd</sub> CL	Propagation Delay from Clear	$V_{CC} = 5V$		250	500	ns
	Input (CL) to Output Q, Q	$V_{CC} = 10V$		120	250	
t <sub>S</sub>	Time Prior to Trigger Input (A, B)	$V_{CC} = 5V$	150	50		ns
	that Clear must be Set	$V_{CC} = 10V$	60	20		
W(A, B)	Trigger Input (A, B) Pulse Width	$V_{CC} = 5V$	150	50		ns
		$V_{CC} = 10V$	70	30		
W(CL)	Clear Input (CL) Pulse Width	$V_{CC} = 5V$	150	50		ns
		$V_{CC} = 10V$	70	30		
W(OUT)	Q or Q Output Pulse Width	$V_{CC} = 5V, R_{EXT} = 10k,$		900		ns
((COT)		$C_{FXT} = 0  pF$				
		$V_{CC} = 10V, R_{EXT} = 10k,$		350		ns
		$C_{FXT} = 0  pF$				
		$V_{CC} = 15V, R_{EXT} = 10k,$		320		ns
		$C_{EXT} = 0  pF$				
		$V_{CC} = 5V, R_{EXT} = 10k,$	9.0	10.6	12.2	μs
		$C_{EXT} = 1000 \text{ pF}$ (Figure 1)				
		$V_{CC} = 10V, R_{EXT} = 10k,$	9.0	10	11	μs
		C <sub>EXT</sub> = 1000 pF (Figure 1)				
		$V_{CC} = 15V, R_{FXT} = 10k,$	8.9	9.8	10.8	μs
		$C_{FXT} = 1000 \text{ pF}$ (Figure 1)				•
		$V_{CC} = 5V, R_{EXT} = 10k,$	900	1020	1200	μs
		$C_{EXT} = 0.1 \ \mu\text{F} (Figure 3)$				
		$V_{CC} = 10V, R_{EXT} = 10k,$	900	1000	1100	μs
		$C_{EXT} = 0.1 \ \mu\text{F}$ (Figure 3)				
		$V_{CC} = 15V, R_{FXT} = 10k,$	900	990	1100	μs
		$C_{EXT} = 0.1 \mu\text{F}$ (Figure 3)		000		μο
R <sub>ON</sub>	ON Resistance of Transistor	$V_{CC} = 5V$ (Note 4)		50	150	
	between R/C <sub>EXT</sub> to C <sub>EXT</sub>	$V_{CC} = 10V$ (Note 4)		25	65	Ω
	Settled HTO EXT to DEXT	$V_{CC} = 15V$ (Note 4)		16.7	45	
	Output Duty Cycle	R = 10k, C = 1000  pF		10.7	43 90	
	Culput Duty Cycle	R = 10k, C = 1000  pr R = 10k, C = 0.1 µF			90 90	%
		(Note 5)			30	
CIN	Input Capacitance	R/C <sub>EXT</sub> Input (Note 6)		15	25	
-IN		Any Other Input (Note 6)		15 5	20	pF

Note 4: See AN-138 for detailed explanation R<sub>ON</sub>.

Note 5: Maximum output duty cycle =  $R_{EXT}/R_{EXT}$  + 1000.

Note 6: Capacitance is guaranteed by periodic testing.





